

# PATENT ABSTRACTS OF JAPAN

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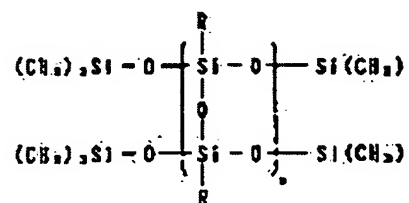
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## (54) NEGATIVE RESIST COMPOSITION

### (57)Abstract:

PURPOSE: To increase sensitivity of a compsn. for deep UV light by using a specified ladder type silicone resin and a specified photosensitive material.

CONSTITUTION: The compsn. of this invention is constituted of a silicone resin expressed by the formula and benzophenone or 2,2-dimethoxy-2-phenyl acetophenone. In the formula, R is a vinyl, allyl, acryloyl, or methacryloyl group; n is 10W1,000. Concrete examples for the above described resin are silylated polyvinyl silsesquioxane, etc. When the compsn. is used as an upper layer resist in a two layered resist, the sensitivity for deep UV light (e.g. light having 248nm wavelength), is increased, and formation of a submicropattern is possible.



## LEGAL STATUS

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